130 & Nonlinear Elements and Circuits Silicon Diode 10 = Is (e VO/VTHE -1) Is = saturation current \$\approx 10^{-12} A

Vine: thermal voltage VTHE = $\frac{kT}{8}$ T: temperature in kelvins $^{\circ}$ K = $^{\circ}$ C + 273.15 k : Boltmann's constant 1252) = 1.38 × 10 -23 J/0K q: charge of an electron = 1.602 × 10-19 C Ideal Nonlinear Revice $\sqrt{p} = \begin{cases} 1 & \sqrt{p^2} & \text{for } V_D > 0 \\ 0 & \text{otherwise} \end{cases}$ where IK is a positive constant Example: find $V_{\overline{D}}$ and $i_{\overline{D}}$: $V_{\overline{D}} = V_{\overline{D}} = V_{\overline{D}} + (-i_{\overline{D}}) = 0$ $V_{\overline{D}} = V_{\overline{D}} = V_{\overline{D}} + (-i_{\overline{D}}) = 0$ $V_{\overline{D}} = V_{\overline{D}} = V_{\overline{D}} = 0$ $V_{\overline{D}} = V_{\overline{D}} = 0$ $V_{\overline{D}} = V_{\overline{D}} = 0$ $V_{\overline{D}} = 0$ norlysis ad: { V-VD - KVD = 0 for Vo>0 $\frac{V-V_0}{R}=0$ otherwise =) $V_D = \frac{-1 + \sqrt{1 + 4RKV}}{2RK}$ and $\tilde{r}_D = 1K(\frac{-1 + \sqrt{1 + 4RKV}}{2RK})^2$ for $V_0 > 0$ 1=3 Exercise: find i3 = ? (hint: Page 29 and the above example) 4v = $\frac{1}{3}$ | $\frac{1}{3}$ |